

Inventor: Gurtej S. Sandhu et al.

Title: Methods of Forming A Thin Film Transistor

Assignee: Micron Technology, Inc.



**INFORMATION DISCLOSURE STATEMENT**

**PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98**

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of co-pending application Serial No. 09/837,645, filed April 17, 2001. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated:

July 21, 2004

By:

Jennifer J. Taylor  
Jennifer J. Taylor, Ph.D.  
Reg. No. 48,711

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1780	SERIAL NO. 09/902,277		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.			
JUL 21 2004 U.S. PATENT & TRADEMARK OFFICE				FILING DATE July 9, 2001		GROUP 2813	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,320,975	6/1994	Cederbaum et al.	437	44	
	AB	5,334,861	8/1994	Pfiester et al.	257	67	
	AC	5,373,170	12/1994	Pfiester et al.	257	69	
	AD	5,411,909	5/1995	Manning et al.	437	52	
	AE	5,418,393	5,1995	Hayden	257	347	
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	AG	5,212,108	5/18/93	Liu, et al.	437	60	
	AH	5,523,240	6/4/96	Zhang, et al.	437	21	
	AI	5,726,096	3/98	Jung	438	592	
	AJ	4,569,697	7/86	Tsu et al.			
	AK	5,665,611	9/97	Sandhu et al.	438	162	
FOREIGN PATENT DOCUMENTS							
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							Yes
	AL	281054A1	7/90	Germany - Mende, et al.			
	AM						
	AP						
OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)							
	AR		Pollack, G.P. et al., "Hydrogen Passivation of Polysilicon MOSFET's From A Plasma Nitride Source", IEEE, 1984 pp. 408-410				
	AS		Kamins, T.I., "Hydrogenation of Transistors Fabricated in Polycrystalline-Silicon Films", IEEE, 1980, pp. 159-161				
	AT		Seager, C.H. et al., "Studies of the hydrogen passivation of silicon grain boundaries", J.Appl. Phys. 52, February 1981, pp. 1050-1055				
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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Form PTO-1449  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					ATTY. DOCKET NO. MI22-1780	PRIORITY SERIAL NO. 09/837,645		
					APPLICANT Gurtej S. Sandhu et al.			
					PRIORITY FILING DATE April 17, 2001	PRIORITY GROUP 2813		
U.S. TRADEMARK OFFICE								
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate
	AA	5,605,848	2/97	Ngaoaram				
	AB	5,364,803	11/94	Lur et al.				
	AC	5,830,802	11/98	Tseng et al.		438	592	
	AD	5,372,860	12/94	Fehlner et al.		427	578	
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	AG	6,001,675	12/14/99	Sandhu et al.		438	151	
	AH	6,077,732	6/20/00	Sandhu et al.		438	158	
	AI	6,238,957	5/29/01	Sandhu et al.		438	151	
	AJ							
	AK							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
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	AR			Kitajima, H. et al., "Leakage Current Reduction in Sub-Micron Channel Poly-Si TFTs", Extended Abstract - 1991 International Conference on Solid State Devices and Materials, Yokohama, 1991, pp. 174-176				
	AS			Sunada, Takeshi et al., "The Role of Fluorine Termination in the Chemical Stability of HF-Treated Si Surfaces", Dept. of Electrical Engineering, Hiroshima University, Higashi-Hiroshima 724, Accepted for Publication 1990				
EXAMINER				DATE CONSIDERED				
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								